

DATA SHEET

BSP225

P-channel enhancement mode
vertical D-MOS transistor

Product specification
File under Discrete Semiconductors, SC13b

April 1995

P-channel enhancement mode vertical D-MOS transistor

BSP225

FEATURES

- Low $R_{DS(on)}$
- Direct interface to C-MOS, TTL, etc.
- High-speed switching
- No secondary breakdown.

DESCRIPTION

P-channel enhancement mode vertical D-MOS transistor in a miniature SOT223 envelope, intended for use in relay, high-speed and line transformer drivers.

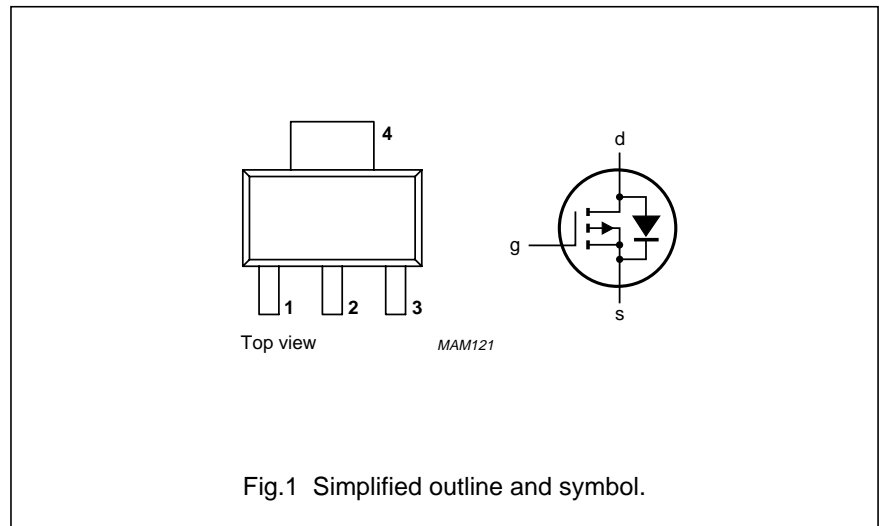
PINNING - SOT223

PIN	DESCRIPTION
1	gate
2	drain
3	source
4	drain

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
$-V_{DS}$	drain-source voltage		250	V
$-I_D$	drain current	DC value	225	mA
$R_{DS(on)}$	drain-source on-resistance	$-I_D = 200 \text{ mA}$ $-V_{GS} = 10 \text{ V}$	15	Ω
$-V_{GS(th)}$	gate-source threshold voltage	$-I_D = 1 \text{ mA}$ $V_{GS} = V_{DS}$	2.8	V

PIN CONFIGURATION



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LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$-V_{DS}$	drain-source voltage		–	250	V
$\pm V_{GSO}$	gate-source voltage	open drain	–	20	V
$-I_D$	drain current	DC value	–	225	mA
$-I_{DM}$	drain current	peak value	–	600	mA
P_{tot}	total power dissipation	up to $T_{amb} = 25\text{ °C}$ (note 1)	–	1.5	W
T_{stg}	storage temperature range		–65	150	°C
T_j	junction temperature		–	150	°C

Note

1. Device mounted on an epoxy printed-circuit board, 40 x 40 x 1.5 mm, mounting pad for the drain lead minimum 6 cm².

THERMAL RESISTANCE

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-a}$	from junction to ambient (note 1)	83.3	K/W

Note

1. Device mounted on an epoxy printed-circuit board, 40 x 40 x 1.5 mm, mounting pad for the drain lead minimum 6 cm².

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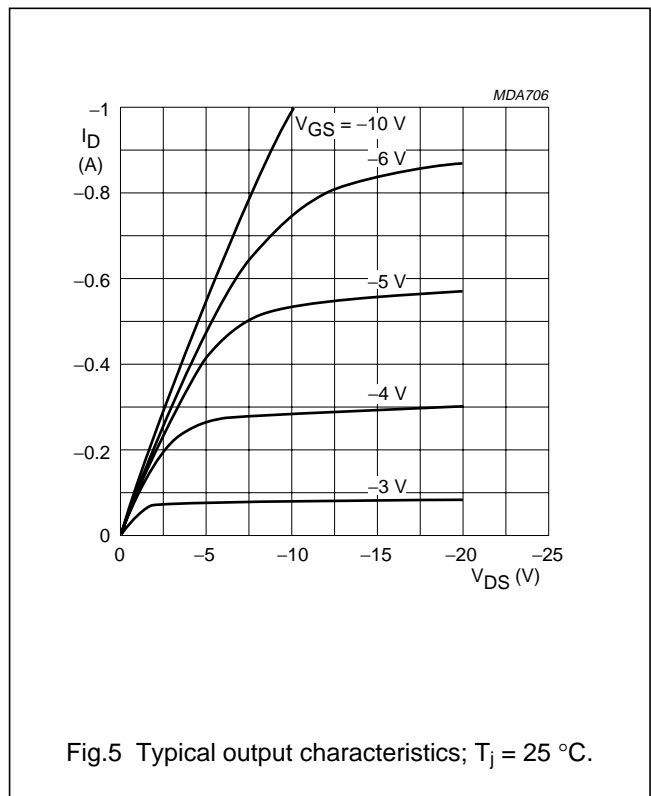
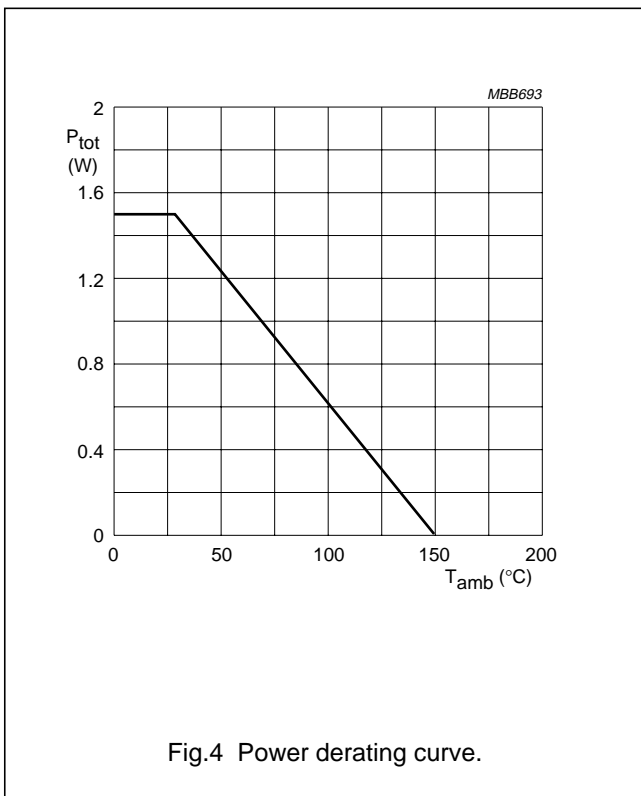
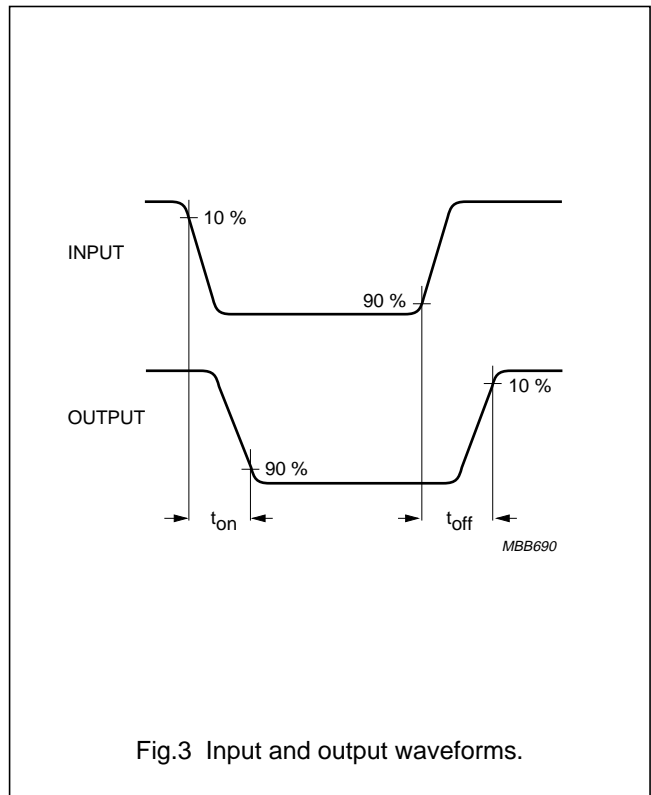
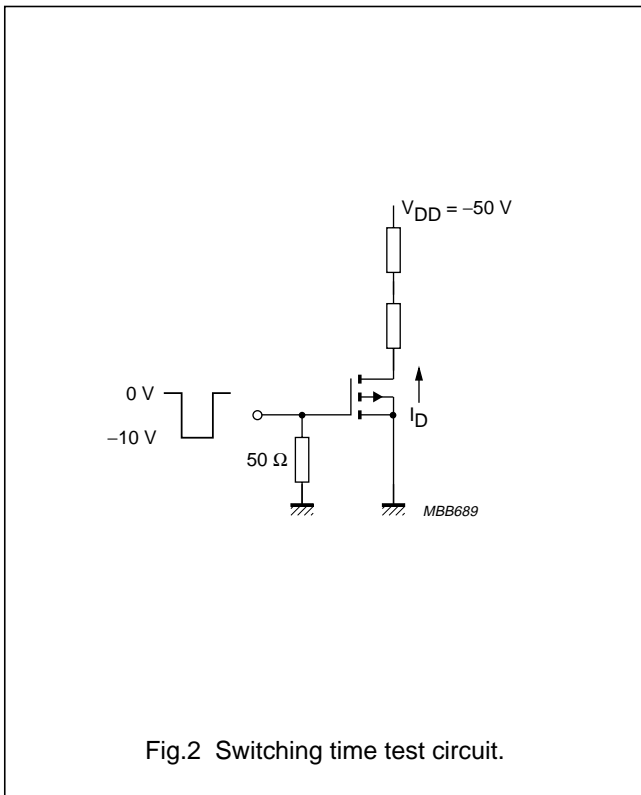
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CHARACTERISTICS $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$-V_{(BR)DSS}$	drain-source breakdown voltage	$-I_D = 10\ \mu\text{A}$ $V_{GS} = 0$	250	–	–	V
$-I_{DSS}$	drain-source leakage current	$-V_{DS} = 200\ \text{V}$ $V_{GS} = 0$	–	–	1	μA
$\pm I_{GSS}$	gate-source leakage current	$V_{DS} = 0$ $\pm V_{GS} = 20\ \text{V}$	–	–	100	nA
$-V_{GS(th)}$	gate-source threshold voltage	$-I_D = 1\ \text{mA}$ $V_{GS} = V_{DS}$	0.8	–	2.8	V
$R_{DS(on)}$	drain-source on-resistance	$-I_D = 200\ \text{mA}$ $-V_{GS} = 10\ \text{V}$	–	10	15	Ω
$ Y_{fs} $	transfer admittance	$-I_D = 200\ \text{mA}$ $-V_{DS} = 25\ \text{V}$	100	200	–	mS
C_{iss}	input capacitance	$-V_{DS} = 25\ \text{V}$ $-V_{GS} = 0$ $f = 1\ \text{MHz}$	–	65	90	pF
C_{oss}	output capacitance	$-V_{DS} = 25\ \text{V}$ $-V_{GS} = 0$ $f = 1\ \text{MHz}$	–	20	30	pF
C_{rss}	feedback capacitance	$-V_{DS} = 25\ \text{V}$ $-V_{GS} = 0$ $f = 1\ \text{MHz}$	–	6	15	pF
Switching times (see Figs 2 and 3)						
t_{on}	turn-on time	$-I_D = 250\ \text{mA}$ $-V_{DD} = 50\ \text{V}$ $-V_{GS} = 0\ \text{to}\ 10\ \text{V}$	–	5	10	ns
t_{off}	turn-off time	$-I_D = 250\ \text{mA}$ $-V_{DD} = 50\ \text{V}$ $-V_{GS} = 0\ \text{to}\ 10\ \text{V}$	–	20	30	ns

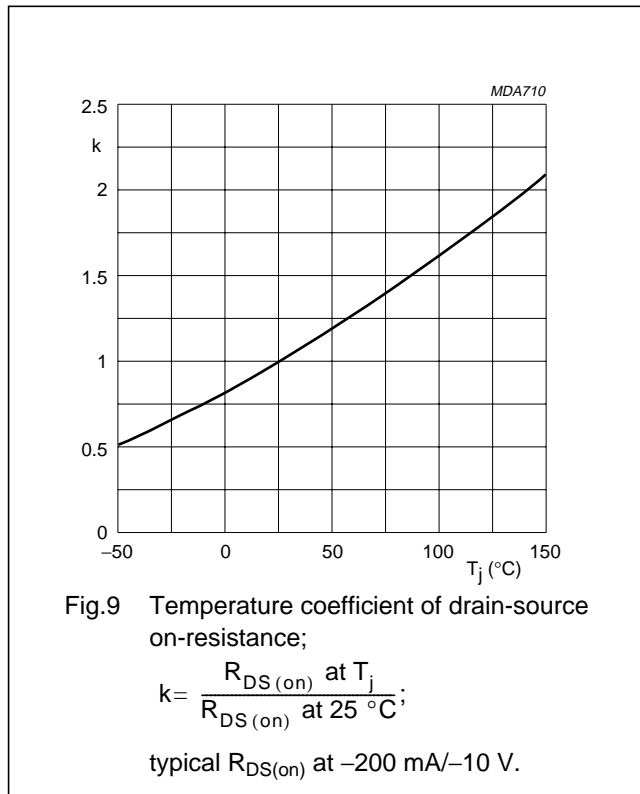
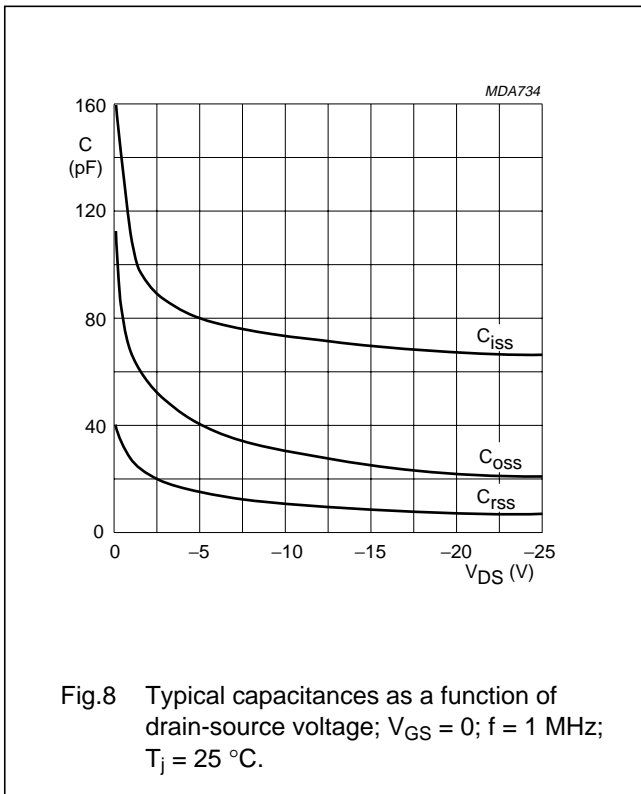
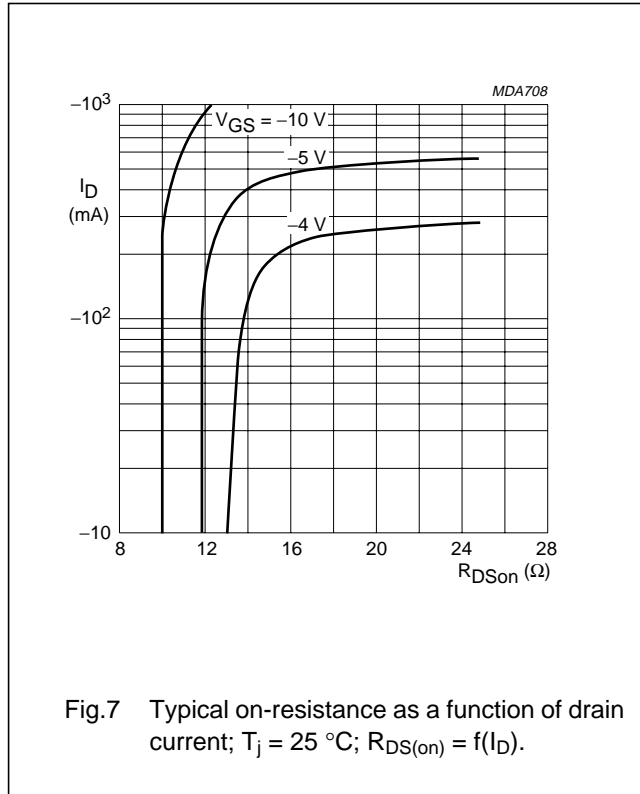
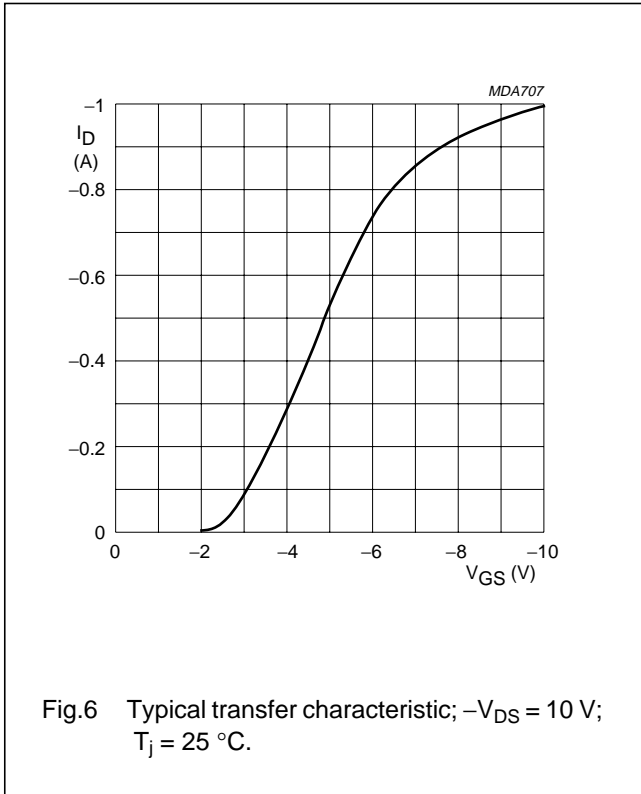
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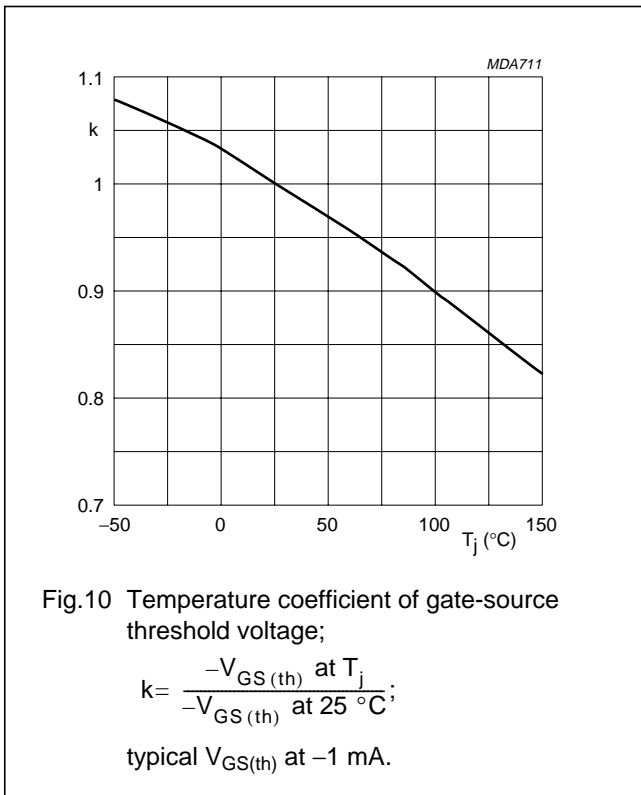
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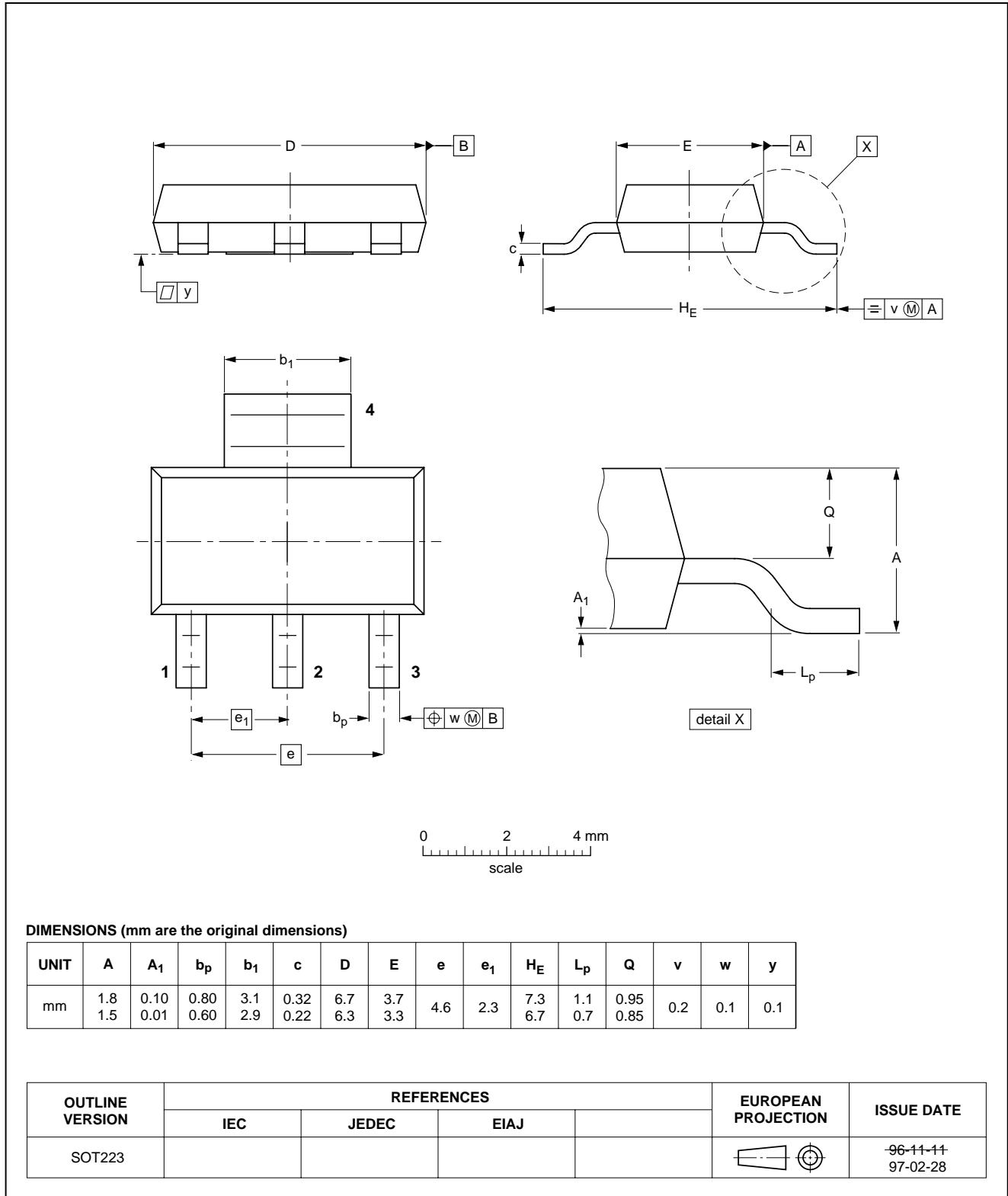
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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



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BSP225**DEFINITIONS**

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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NOTES

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